

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT31B6N3T

CHIP SIZE	0.54 * 0.54 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	51,978 pcs

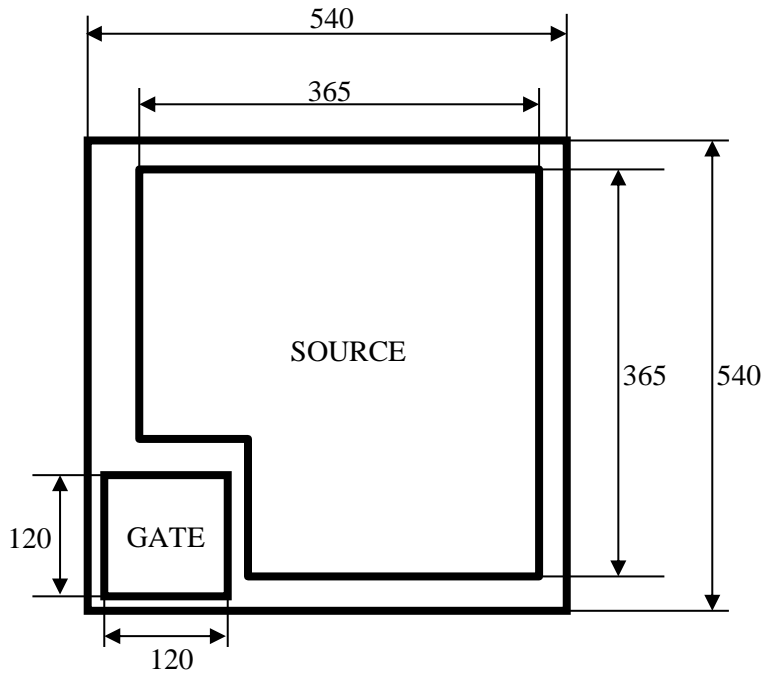
Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	V _{DSS}	60	V
Gate-source voltage	V _{GSS}	±20	V
Drain Current (DC)	I _D	0.5	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			100	nA	V _{GS} = ±20V V _{DS} = 0V
2	IDSS			100	nA	V _{DS} = 62V V _{GS} = 0V
3	BVDSS	63			V	I _D = 10uA
4	V _{TH}	1.5		2.5	V	I _D = 1mA
5	Ron 1		0.4	0.65	Ω	I _D = 250mA V _{GS} = 10V
6	Ron 2		0.5	0.8	Ω	I _D = 250mA V _{GS} = 5V
7	VSD	0.5		1.1	V	I _S = 115mA V _{GS} = 0V
8	Yfs	200			mS	V _{DS} = 10V I _D = 200mA



TENTATIVE

NOTE: